

AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No.: 09/885,943

both the amorphous layer and the crystalline layer being made of boron phosphide (BP),
the gallium nitride phosphide single crystal layer consisting of $\text{GaN}_{0.97}\text{P}_{0.03}$ is formed in
contact with the crystalline layer of boron phosphide, and

a light-emitting layer made of cubic $\text{Ga}_{0.94}\text{In}_{0.06}\text{N}$ is formed on said gallium nitride
phosphide single crystal layer consisting of $\text{GaN}_{0.97}\text{P}_{0.03}$.